

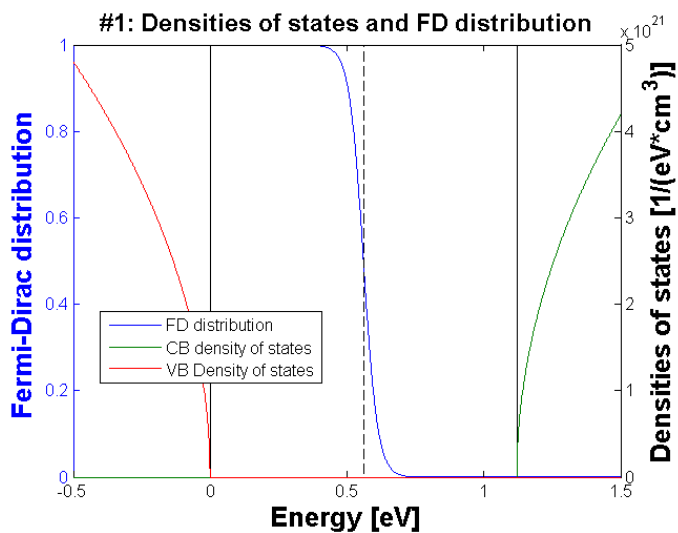
TN2624 MATLAB Session 11

Solutions

May 23, 2013

Semiconductor statistics Part 1 – the intrinsic semiconductor (70 pts)

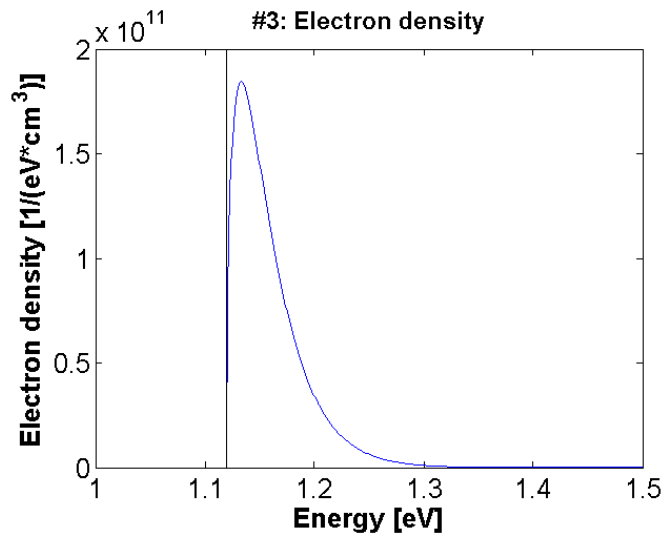
1. (25 pts) Fermi-Dirac distribution and density of states as a function of energy.



2. (5 pts) The same as the distribution for the electrons, but mirrored at the chemical potential

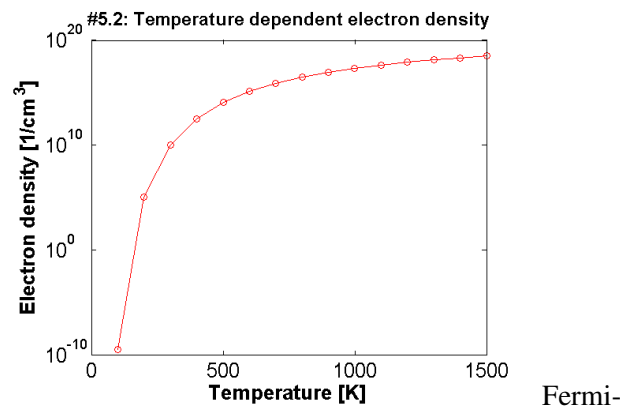
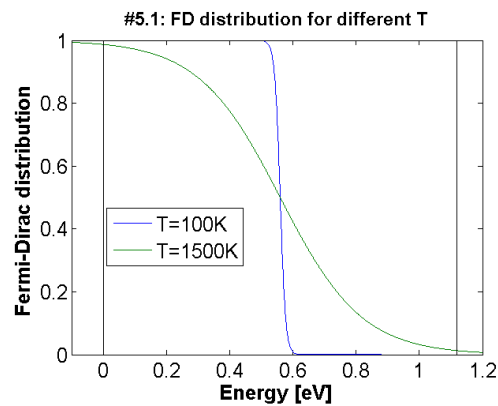
$$\bar{n}_{\text{FD,h}}(E) = \frac{1}{1 + \exp \frac{\mu - E}{kT}}.$$

3. (10 pts)



4. (5 pts) %Result: $9.8506 \times 10^9 \text{ 1/cm}^3$, way too low

5. (25 pts)



Dirac distribution “smears out” at higher temperatures → more electrons excited to the conduction band

Unrealistically high temperatures would be required to obtain significant electron densities

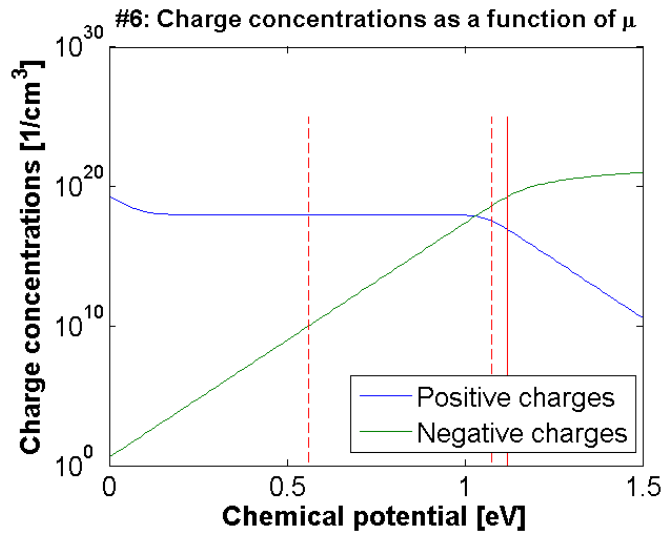
Semiconductor statistics Part 2 – the doped semiconductor (30 pts)

6. (20 pts)

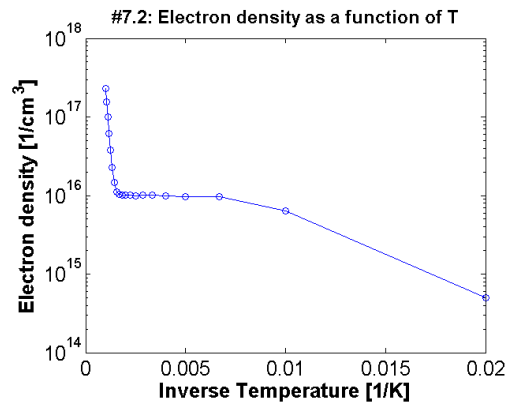
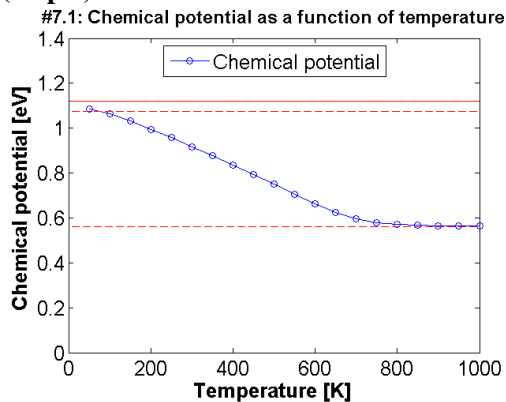
$\mu = 1.0300 \text{ eV}$,

$n = 7.6210 \times 10^{17} \text{ cm}^{-3}$,

$p = 125.9659 \text{ cm}^{-3}$, virtually no holes in the valence band... all electrons stem from the dopants



7. (10 pts)



- Low temperature: The electrons from the dopants get excited to the conduction band
- Medium temperature: All the dopants have been activated (electron density saturates to dopant density), yet the temperature is still too low to excite electrons from the valence band to the conduction band
- High temperature: Electrons can be excited from the valence band to the conduction band